L Number	Hits	Search Text	DB	Time stamp
279	0	5866263.URPN.	USPAT	2002/08/13 11:37
280	4	("4427992" "4900646" "5250845" "5401536").PN.	USPAT	2002/08/13 11:37
281	6	4427992.URPN.	USPAT	2002/08/13 11:39
282	6	4427992.URPN.	USPAT	2002/08/13 11:41
283	4	("2683667" "3528169" "3586926" "3789023").PN.	USPAT	2002/08/13 11:41
285	13	1 3586926.URPN.	USPAT	
294	1	5869560.URPN.	USPAT	2002/08/13 11:42
295	6			2002/08/13 11:47
		("5314941" "5416146" "5446064" "5478882" "5523355" "5554683").PN.	USPAT	2002/08/13 11:47
712	55	(adsorb\$3 adsorption) with ((("si" silicon) with (fluorine))or si\$2f)	EPO; JPO; DERWENT	2002/08/13 15:55
720	10	(adsorb\$3 adsorption) with ((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	USPAT; US-PGPUB; IBM_TDB	2002/08/13 15:55
724	8	(adsorb\$3 adsorption) with ((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	EPO; JPO; DERWENT	2002/08/13 12:45
716	102	(adsorb\$3 adsorption) with ((("si" silicon) with (fluorine))or si\$2f)	USPAT; US-PGPUB; IBM TDB	2002/08/13 14:19
728	0	(adsorb\$3 adsorption) with (si\$1f) with bond	EPO; JPO; DERWENT	2002/08/13 14:24
732	0	(adsorb\$3 adsorption) with "si-f" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
736	0	(adsorb\$3 adsorption) with "sif" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
740	0	(adsorb\$3 adsorption) with "sif" with bond	EPO; JPO; DERWENT	2002/08/13 14:24
744	4	(adsorb\$3 adsorption) with "sif" with bond	USPAT; US-PGPUB; IBM TDB	2002/08/13 14:26
748	100	(adsorb\$3 adsorption) with silicon with fluori\$3	USPAT; US-PGPUB;	2002/08/13 14:26
752	0	(adsorb\$3 adsorption) with silicon with fluori\$3 with (organic with carbon)	IBM_TDB USPAT; US-PGPUB;	2002/08/13 14:27
760	9	(adsorb\$3 adsorption) with silicon with fluori\$3 with (organic carbon)	IBM_TDB USPAT; US-PGPUB;	2002/08/13 14:27
756	10	((adsorb\$3 adsorption) with silicon with fluori\$3) same (organic carbon)	IBM_TDB USPAT; US-PGPUB;	2002/08/13 14:27
769	1		IBM_TDB USPAT; US-PGPUB; JPO;	2002/08/13 14:37
774	37	method same ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:41
784	0	("gate oxide" with polysilicon with hole) and ((stor\$3 transfer\$3) with (adsorb\$4 adsorp\$4))	DERWENT IBM_TDB	2002/08/13 14:42
779	1	("gate oxide" with polysilicon with hole) and ((stor\$3 transfer\$3) with (adsorb\$4 adsorp\$4))	USPAT; US-PGPUB;	2002/08/13 14:43
785	2	("gate oxide" with polysilicon with hole) and (adsorb\$4 adsorp\$4)	JPO; DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 14:45
790	0	("gate oxide" with polysilicon with hole) and (adsorb\$4 adsorp\$4)	DERWENT IBM_TDB	2002/08/13 14:44

				
791	9	(gate with polysilicon with hole) and (adsorb\$4 adsorp\$4)	USPAT; US-PGPUB;	2002/08/13 14:48
796 797	0 699	(gate with polysilicon with hole) and (adsorb\$4 adsorp\$4) adsorbent with between with process\$3	JPO; DERWENT IBM_TDB USPAT; US-PGPUB;	2002/08/13 14:48 2002/08/13 15:01
802	25	adsorbent with between with process\$3 with (film deposit\$3 layer)	JPO; DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:03
807	31	adsorbent with between with process\$3 with (semiconductor wafer substrate film deposit\$3 layer)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:07
812	313	(adsorbent adsorb adsorption) with between with (process\$3 step method) with (semiconductor wafer substrate film deposit\$3 layer)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:15
817	51	(adsorbent adsorb adsorption) with between with (process\$3 step method) with (semiconductor wafer substrate film deposit\$3 layer) with (carbon organic)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:17
822	0	118/719.ccls. and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:42
827	0	(multi\$4 with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:43
828	0	((multi multiple) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:44
833	0	((transfer) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:44
838	1	((transfer\$3 stor\$3) with chamber) and ("gate oxide" with polysilicon with hole)	DERWENT USPAT; US-PGPUB; JPO;	2002/08/13 15:45
843	19	(absorb) with ((("si" silicon) with (fluorine))or si\$2f)	DERWENT EPO; JPO; DERWENT	2002/08/13 15:56
851	65	(absorb\$3) with ((("si" silicon) with (fluorine))or si\$2f)	EPO; JPO;	2002/08/13 16:06
847	14	(absorb\$3) with ((("si" silicon) with (fluorine))or si\$2f) with (organic or carbon)	DERWENT USPAT; US-PGPUB;	2002/08/13 15:57
855	38983	"11259078" c23c016\$.ipc.	IBM_TDB JPO JPO;	2002/08/13 18:16 2002/08/12 12:36
-	660865	h01l021\$.ipc.	DERWENT JPO;	2002/08/12 12:36
-	117	(156/345.31).CCLS.	DERWENT USPAT;	2002/08/12 12:16
-	О	(156/345.31 and (adsorb adsorption absorb)).CCLS.	US-PGPUB USPAT;	2002/08/12 12:17
_	23	156/345.31.ccls. and (adsorb adsorption absorb)	US-PGPUB USPAT; US-PGPUB	2002/08/12 12:26
			- CO 1 OI OI	

		1/440/245 200		
. -	169		USPAT;	2002/08/12 12:30
		adsorption absorb) with (cassette vessel apparatus store	US-PGPUB	
		storage transfer stock))		
-	0	0 "08346836"	USPAT;	2002/08/12 12:30
			US-PGPUB;	
			EPO; JPO;	
_	1 0	"08-346836"	DERWENT	
		00-340030	USPAT;	2002/08/12 12:29
			US-PGPUB;	
			EPO; JPO;	
-	1 0	"080346836"	DERWENT	0000/00//
İ			USPAT;	2002/08/12 12:29
			US-PGPUB; EPO; JPO;	
			DERWENT	
-	0	10-181881	USPAT;	2002/08/12 12:30
•			US-PGPUB;	2002/06/12 12:30
	İ		EPO; JPO;	
			DERWENT	
-	2	container with seal with adsorbing	EPO; JPO;	2002/08/12 12:32
			DERWENT	2002/00/12 12.02
-	1	semiconductor with adsorbing with contaminants	EPO; JPO;	2002/08/12 12:34
			DERWENT	1202/05/12 12:04
-	1	clarification with degree with sealing	EPO; JPO;	2002/08/12 12:35
	40400	-00 0400 :	DERWENT	
-	40400	c23c016\$.ipc.	JPO;	2002/08/12 12:36
1_	677126	h0410040 :	DERWENT	
-	677136	h01l021\$.ipc.	JPO;	2002/08/12 12:36
-	1320	(02300169 inc. h0410040 inc.)	DERWENT	
	1320	(c23c016\$.ipc. h01l021\$.ipc.) and ((adsorb\$3 adsorption	EPO; JPO;	2002/08/12 12:38
		absorb) with (cassette vessel apparatus store storage transfer stock container))	DERWENT	
-	187	(118/715-733.ccls. 156/345.1-345.55.ccls.) and ((adsorb\$3		
	, , ,	adsorption absorb) with (cassette vessel apparatus store	USPAT;	2002/08/12 15:01
}		storage transfer stock container))	US-PGPUB	
-	760	(c23c016\$.ipc. h01l021\$.ipc.) and (((adsorb\$3 adsorption	EDO: IDO:	0000100110 10 00
ĺ		absorb) with (cassette vessel apparatus store storage	EPO; JPO; DERWENT	2002/08/12 12:39
	1	transfer stock container)) same (semiconductor wafer	DEKANEINI	
	J	substrate))		
-	391	(c23c016\$.ipc. h01l021\$.ipc.) and (((adsorb\$3 adsorption	EPO; JPO;	2002/08/12 13:48
		absorb) with (cassette vessel apparatus store storage	DERWENT	2002/00/12 13.46
		transfer stock container)) same (stor\$3 transfer\$3))		
-	8	(c23c016\$.ipc. h01l021\$.ipc.) and (((adsorb\$3 adsorption	EPO; JPO;	2002/08/12 12:49
		absorb) with (cassette vessel apparatus store storage	DERWENT	
		transfer stock container)) same (stor\$3 transfer\$3) same		
-	1	organic) ("5863808").PN.]
		(0000000).FIV.	USPAT;	2002/08/12 12:50
-	2	("5105628" "5551984"), PN.	US-PGPUB	
-	0	5863808.URPN.	USPAT	2002/08/12 13:01
-	26	"0259078"	USPAT	2002/08/12 13:02
			EPO; JPO;	2002/08/12 13:57
-	27	"0259078"	DERWENT	0000100115
			USPAT;	2002/08/12 13:57
1			US-PGPUB;	
1	1 [EPO; JPO; DERWENT	ļ
-	4958	(adsorb\$3 adsorption) with (cassette vessel apparatus store	USPAT:	2002/09/42 45:00
	l i	storage transfer stock container) with (stor\$3 transfer\$3)	US-PGPUB	2002/08/12 15:00
[-	2582	(adsorb\$3 adsorption) with (cassette vessel apparatus	USPAT;	2002/08/12 15:01
	1 1	storage stock container) with (stor\$3 transfer\$3)	US-PGPUB	2002/00/12 10:01
-	8	(118/715-733.ccls. 156/345.1-345.55.ccls.) and ((adsorb\$3	USPAT;	2002/08/12 15:37
		adsorption) with (cassette vessel apparatus storage, stock	US-PGPUB	
_		container) with (stor\$3 transfer\$3))		
_	1	("4851018").PN.	USPAT;	2002/08/12 15:03
	<u> </u>		US-PGPUB	

,		4054040 LIDDN	LIGHT	T 0000/00/40 45 00
,-	29	4851018.URPN.	USPAT	2002/08/12 15:03
-	590	((adsorb\$3 adsorption) with (cassette vessel apparatus	USPAT;	2002/08/12 15:39
		storage stock container) with (stor\$3 transfer\$3)) same	US-PGPUB	
	1	(carbon organic)		
-	104	((adsorb\$3 adsorption) with (cassette vessel apparatus	USPAT;	2002/08/12 16:08
		storage stock container) with (stor\$3 transfer\$3)) same	US-PGPUB	
		(semiconductor wafer substrate)		
-	7	5498118.URPN.	USPAT	2002/08/12 15:45
-	4	6048655.URPN.	USPAT	2002/08/12 15:46
-	11	("4539695" "4758127" "4770590" "4984953" "5026239"	USPAT	2002/08/12 15:47
		"5102280" "5183370" "5301013" "5308222" "5405230"		
		"5498118").PN.		
-	6	("4178113" "4493606" "4550242" "4759681" "4938655"	USPAT	2002/08/12 15:48
		"4988252").PN.		
-	27	5183370.URPN.	USPAT	2002/08/12 15:49
-	0	20010027028.URPN.	USPAT	2002/08/12 16:01
-	8	("4471716" "4724874" "4963069" "5207548" "5255797"	USPAT	2002/08/12 16:07
		"5346518" "5749469" "5843196").PN.		
-	1	((adsorb\$3 adsorption) and (("4471716" "4724874"	USPAT;	2002/08/12 16:13
		"4963069" "5207548" "5255797" "5346518" "5749469"	US-PGPUB	
		"5843196").PN.))		
-	16	5346518.ÚRPN. ´	USPAT	2002/08/12 16:12
-	8	((adsorb\$3 adsorption) and 5346518.URPN.)	USPAT;	2002/08/12 16:15
		(, , , , , , , , , , , , , , , , , , ,	US-PGPUB	
_	1067	(adsorb\$3 adsorption) same(("si" silicon) with (wafer	USPAT;	2002/08/12 16:17
		substrate))	US-PGPUB	
_	17	(adsorb\$3 adsorption) same(("si" silicon) with (wafer	USPAT;	2002/08/12 16:29
		substrate) with (coat\$3 deposit\$3 film) with (fluorine si\$1f))	US-PGPUB	2002/00/12 10:20
-	319	(adsorb\$3 adsorption) with ("si" silicon) with (wafer	USPAT;	2002/08/12 16:36
1		substrate) with (coat\$3 deposit\$3 film treat\$3)	US-PGPUB	2002/00/12 10:00
l -	0	118/&.ccls. and((adsorb\$3 adsorption) with ("si" silicon) with	USPAT;	2002/08/12 16:36
		(wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	US-PGPUB	2002/00/12 10:00
<u>-</u>	210	((adsorb\$3 adsorption) with ("si" silicon) with (wafer	EPO; JPO;	2002/08/12 16:39
		substrate) with (coat\$3 deposit\$3 film treat\$3))	DERWENT	2002/00/12 10:55
_	9	118/\$.ccls. and((adsorb\$3 adsorption) with ("si" silicon) with	USPAT;	2002/08/12 16:37
		(wafer substrate) with (coat\$3 deposit\$3 film treat\$3))	US-PGPUB	2002/00/12 10.5/
_	119	(c23c016\$.ipc. h01l021\$.ipc.) and ((adsorb\$3 adsorption)	EPO; JPO;	2002/08/13 09:49
		with ("si" silicon) with (wafer substrate) with (coat\$3	DERWENT	2002/00/15 09.49
		deposit\$3 film treat\$3))	DER.	
-	10	(c23c016\$.ipc. h01l021\$.ipc.) and ((adsorb\$3 adsorption)	EPO; JPO;	2002/08/13 09:18
		with ("sif" "si-f" ((silicon "si") with ("f" fluorine))) with (wafer	DERWENT	2002/00/10 03.10
		substrate) with (coat\$3 deposit\$3 film treat\$3))	DERVICIVI	
-	6	((adsorb\$3 adsorption) with ("si" silicon) with (wafer	EPO; JPO;	2002/08/13 09:50
		substrate) with (transfer\$3 stor\$3))	DERWENT	2002/00/13 09.50
<u>-</u>	13	((adsorb\$3 adsorption) with ("si" silicon) with (wafer	USPAT;	2002/08/13 10:05
		substrate) with (transfer\$3 stor\$3))	US-PGPUB	2002/00/13 10:03
_	47	((adsorb\$3 adsorption) with ("si" silicon) with (transfer\$3	USPAT;	2002/08/13 10:13
	1 "	stor\$3))	US-PGPUB	2002/00/10 10.10
_	25	((adsorb\$3 adsorption) with ("si" silicon) with (transfer\$3	EPO; JPO;	2002/08/13 12:29
	-5	stor\$3))	DERWENT	2002/00/13 12.29
_	610	((adsorb\$3 adsorption) with ("si" silicon) with (wafer	USPAT;	2002/08/13 10:19
		substrate semiconductor))	US-PGPUB	2002/00/13 10.19
L		Table of the original of the o	1 20-1 GF 0D	